

General Description

The CMSC3812A uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. The two MOSFETs make a compact and efficient switch and synchronous rectifier combination for use in buck converters.

Features

- Low On-Resistance
- Improved dv/dt capability
- Fast switching
- RoHS Compliant

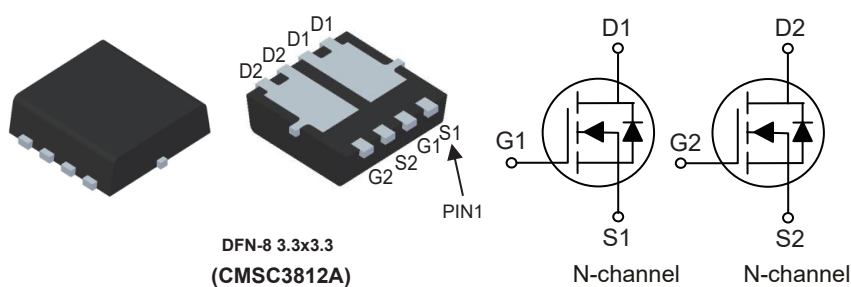
Product Summary

BVDSS	$R_{DS(on)}$ max.	ID
30V	22mΩ	20A

Applications

- DC/DC Converters in Computing, Servers, and POL
- Isolated DC/DC Converters in Telecom and Industrial

DFN-8 3.3x3.3 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Continuous Drain Current	20	A
$I_D@T_A=75^\circ\text{C}$	Continuous Drain Current	13	A
I_{DM}	Pulsed Drain Current	80	A
EAS	Single Pulse Avalanche Energy ¹	36	mJ
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation	25	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	---	62	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-case	---	5	°C/W

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	30	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=12A$	---	19	22	mΩ
		$V_{GS}=4.5V$, $I_D=10A$	---	36	44	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1	---	3	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=30V$, $V_{GS}=0V$	---	---	1	μA
		$V_{DS}=24V$, $V_{GS}=0V$, $T_J=125^{\circ}\text{C}$	---	---	10	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=10A$	---	9	---	S
Q_g	Total Gate Charge	$V_{DS}=15V$, $I_D=8A$ $V_{GS}=4.5V$	---	4	---	nC
Q_{gs}	Gate-Source Charge		---	1	---	
Q_{gd}	Gate-Drain Charge		---	2.1	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V$, $V_{GS}=10V$, $R_G=6\Omega$ $I_D=1A$	---	3	---	ns
T_r	Rise Time		---	7.5	---	
$T_{d(off)}$	Turn-Off Delay Time		---	16	---	
T_f	Fall Time		---	5	---	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	600	---	pF
C_{oss}	Output Capacitance		---	100	---	
C_{rss}	Reverse Transfer Capacitance		---	50	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Diode continuous forward current	$V_G=V_D=0V$, Force Current	---	---	20	A
$I_{S,pulse}$	Diode pulse current		---	---	80	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_F=1A$, $T_J=25^{\circ}\text{C}$	---	---	1	V

Notes:

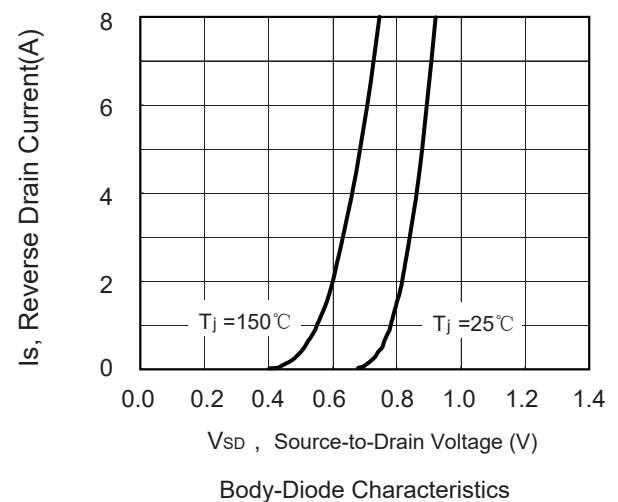
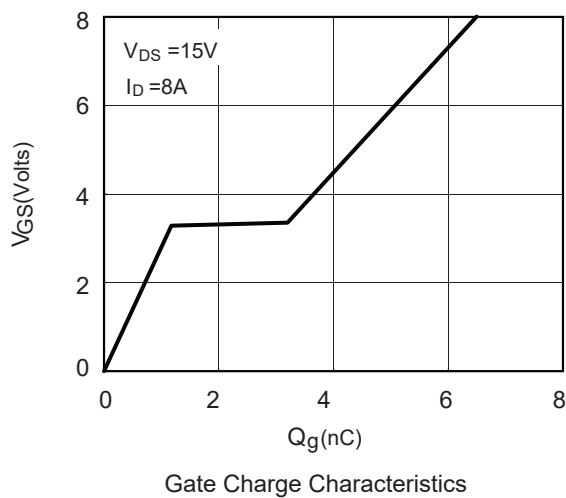
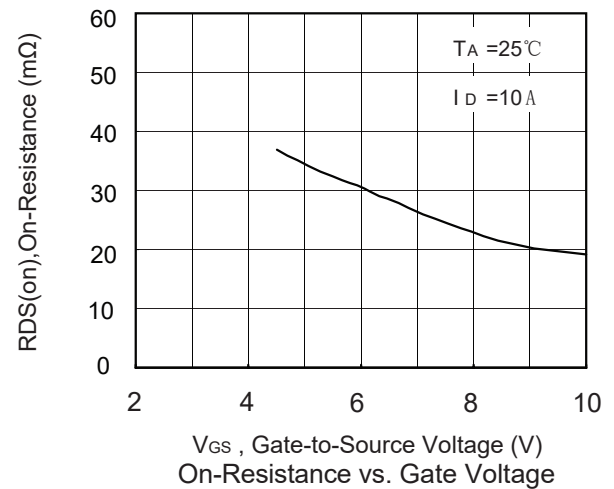
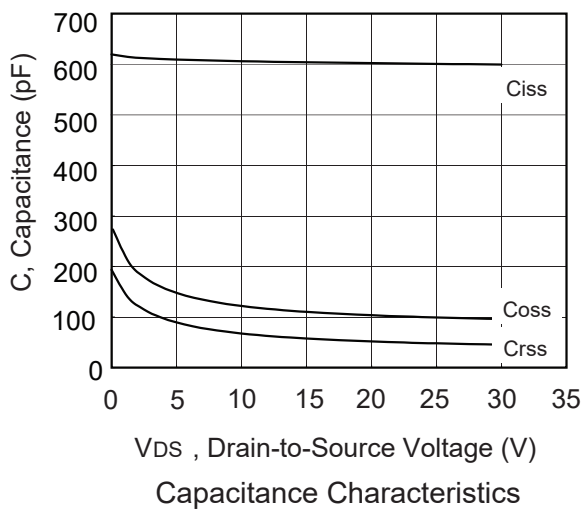
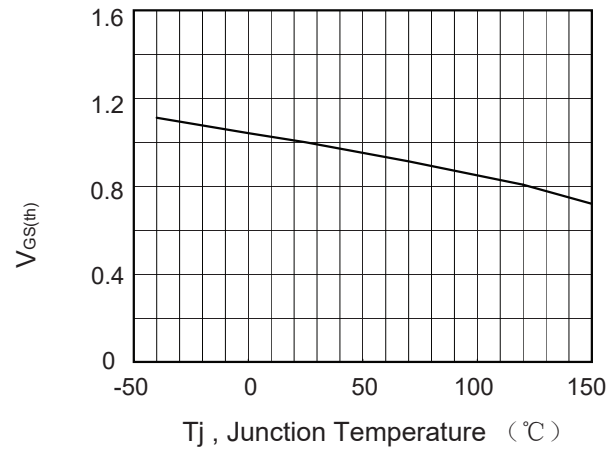
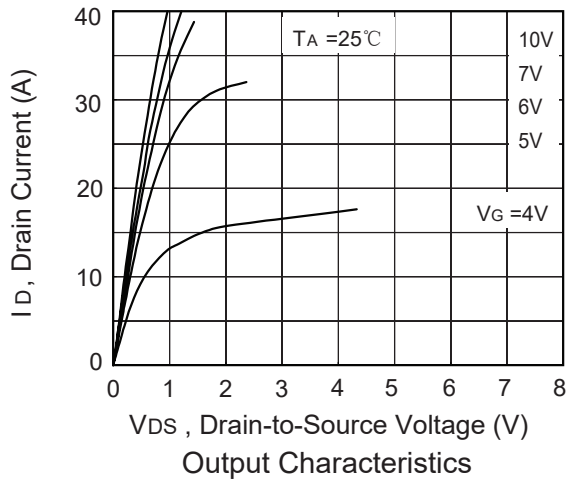
1.The EAS data shows Max. rating .The test condition is $V_{DS}=25V$, $V_{GS}=10V$, $L=0.5\text{mH}$, $I_{AS}=12A$.

This product has been designed and qualified for the consumer market.

Cmos assumes no liability for customers' product design or applications.

Cmos reserves the right to improve product design ,functions and reliability without notice.Please refer to the latest version of specification.

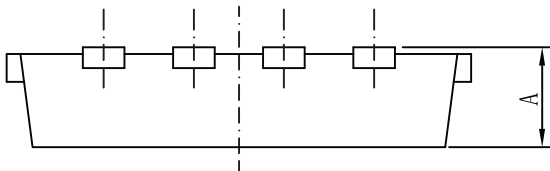
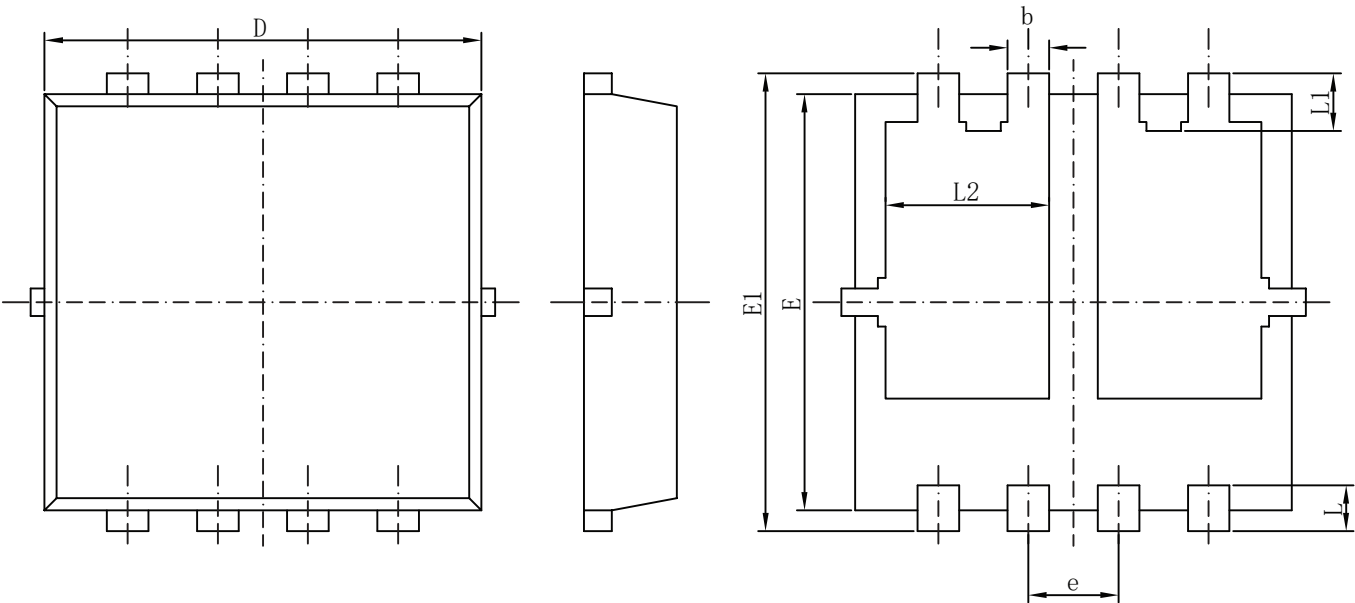
Typical Characteristics



Package Dimension

DFN-8 3.3X3.3 Dual

Unit :mm



- 注：
- 1. 未注公差±0.10
 - 2. 塑封体无缺损、缩孔、裂纹、气泡等不良缺陷
 - 3. 标注单位mm

Dimensions In Millimeters			
Symbol	Min.	Max.	Ave.
A	0.700	0.900	0.800
D	3.000	3.200	3.100
E	3.000	3.200	3.100
E1	3.200	3.600	3.400
b	0.200	0.400	0.300
e	0.550	0.750	0.650
L	0.300	0.600	0.450
L1	0.395	0.695	0.545
L2	0.885	1.185	1.035